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UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,812,535 B2
DATED : November 2, 2004
INVENTOR(S) : Yagishita et al.

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

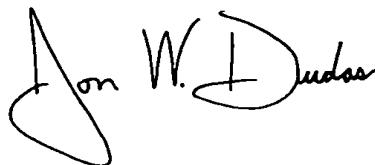
Title page.

Item [57], **ABSTRACT**, delete in its entirety and insert therefor:

-- A semiconductor device with a source and drain formed in a semiconductor substrate; a crystallized gate insulating film formed on the substrate in a region between the source semiconductor and drain; gate electrode formed on the gate insulating film; an insulating film formed on a side surface of the gate electrode and having an amorphous structure formed from the same material as that of the gate insulating film. Furthermore the insulating film is essentially formed from a material selected from the group consisting of cerium oxide (CeO_2), zirconium oxide (ZrO_2), hafnium oxide (HfO_2), thorium oxide (ThO_2), yttrium oxide (Y_{2}O_3), calcium fluoride (CaF_2), tin-calcium fluoride (CaSnF_2), titanium-barium oxide (BaTiO_2), and La_2O_3 . --.

Signed and Sealed this

Fifteenth Day of February, 2005



JON W. DUDAS
Director of the United States Patent and Trademark Office